

AUFI3205-VB Datasheet

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a
60	0.005 at $V_{GS} = 10$ V	120
	0.013 at $V_{GS} = 4.5$ V	95

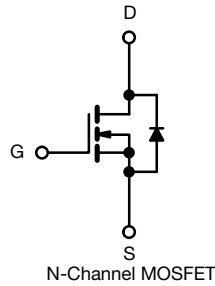
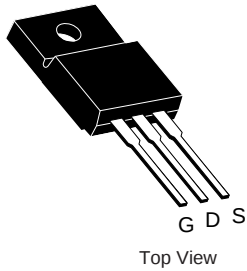
FEATURES

- 175 °C Junction Temperature
- Trench Power MOSFET
- Material categorization:



RoHS
COMPLIANT

TO-220 FULLPAK



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_J = 175$ °C) ^b	I_D	120	A
		95 ^a	
Pulsed Drain Current	I_{DM}	300	
Continuous Source Current (Diode Conduction)	I_S	70 ^a	
Avalanche Current	I_{AS}	50	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	E_{AS}	125	mJ
Maximum Power Dissipation	P_D	136	W
		3 ^b , 8.3 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	15	18	°C/W
		40	50	
Maximum Junction-to-Case	R_{thJC}	0.85	1.1	

Notes:

- a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. $t \leq 10$ s.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1	2	3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	60			A
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.005		Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.010		
		V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C		0.015		
		V _{GS} = 4.5 V, I _D = 15 A		0.013		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		5650		pF
Output Capacitance	C _{oss}			1120		
Reverse Transfer Capacitance	C _{rss}			525		
Total Gate Charge ^c	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 50 A		47	70	nC
Gate-Source Charge ^c	Q _{gs}			10		
Gate-Drain Charge ^c	Q _{gd}			12		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.6 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _g = 2.5 Ω		10	20	ns
Rise Time ^c	t _r			15	25	
Turn-Off Delay Time ^c	t _{d(off)}			35	50	
Fall Time ^c	t _f			20	30	
Source-Drain Diode Ratings and Characteristics (T _C = 25 °C)						
Pulsed Current	I _{SM}			300		A
Diode Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		1	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		45	100	ns

Notes:

- For design aid only; not subject to production testing.
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C unless noted)



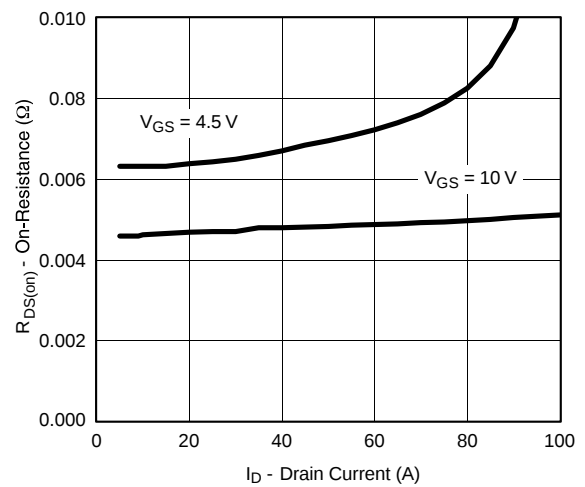
Output Characteristics



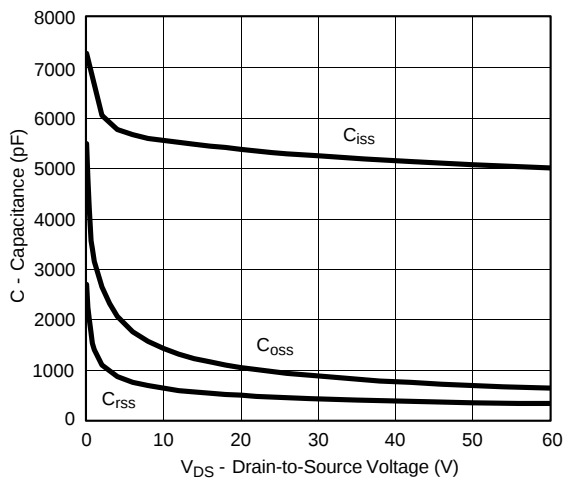
Transfer Characteristics



Transconductance



On-Resistance vs. Drain Current

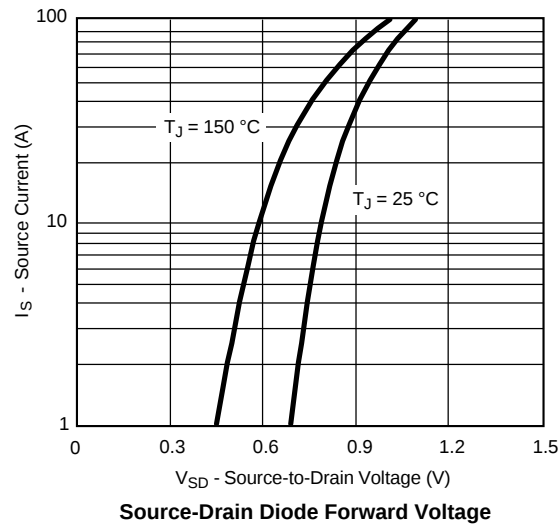


Capacitance

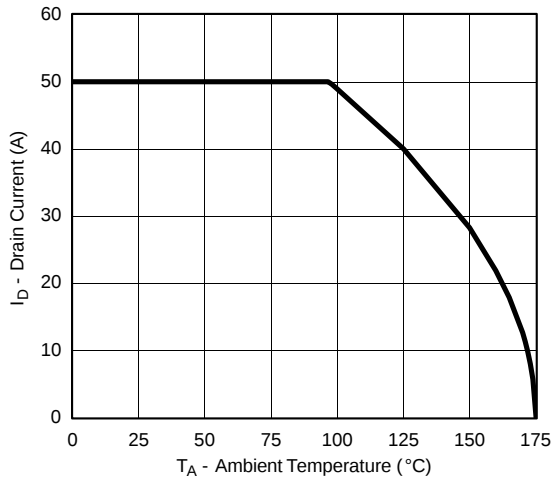


Gate Charge

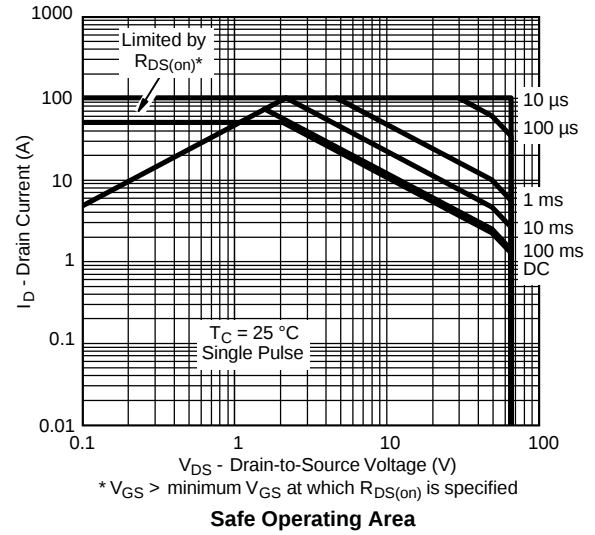
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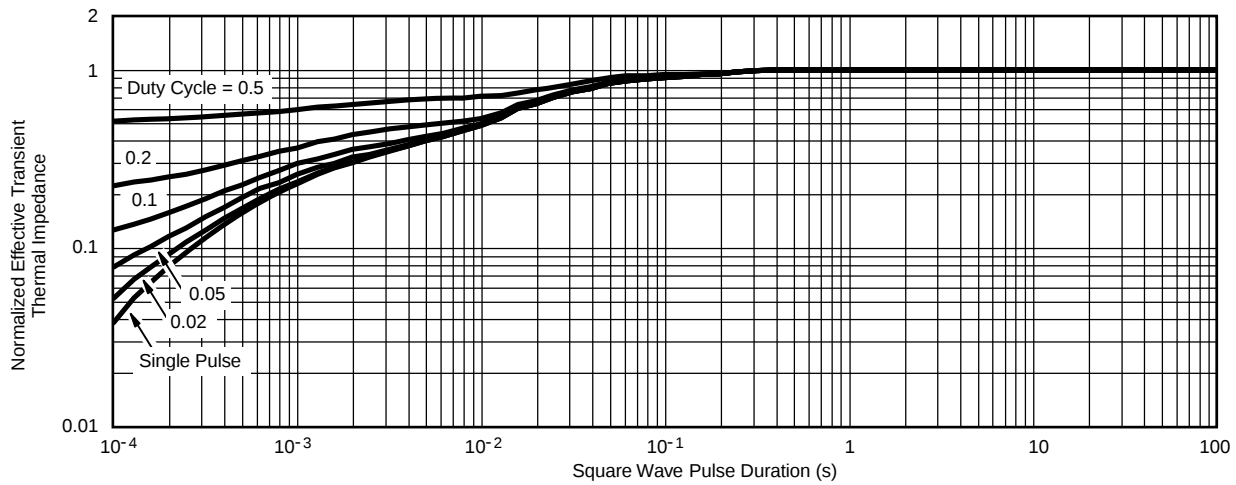
THERMAL RATINGS



Maximum Drain Current vs. Ambient Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-220 FULLPAK (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
v	0.400	0.500	0.016	0.020

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DWG: 5972

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet $C_{pk} > 1.33$.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.

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